



信昌電子陶瓷股份有限公司
Prosperity Dielectrics Co., Ltd.

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Messrs. : _____

Date : _____

APPROVAL SHEET

Product Name : Stacked Capacitors

Part No. : FE Series

Description : Size 1210~2225, C0G/X7R, 50Vdc to 1000Vdc

PREPARED BY	APPROVED BY

信昌電子陶瓷股份有限公司

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SPECIFICATION

FOR

Product Name : Stacked Capacitors
Part No. : FE Series
Description : Size 1210~2225, C0G/X7R, 50Vdc to 1000Vdc

SPEC. No. : <u>FE-000-001-03</u>
DATE :

DRAWN BY	CHECEKED BY	APPROVED BY
Yvens Chou	Yvens Chou	Ryan Chen



1. INTRODUCTION

FE Series green type capacitors are manufactured by using green materials without lead and cadmium. These capacitors to achieve a unique structure of high reliability. The use of metal lead frame, can absorb the heat and mechanical stress. ESR (equivalent series resistance), ESL (equivalent series inductance) is small, the most suitable for high frequency operation of the rectifier power supply.

2. FEATURES

- High reliability and stability.
- Higher mechanical endurance.
- Anti thermal stress and mechanical stress.
- Improved vibration performance.
- More capacitance without changing footprint.
- RoHS Compliant.

3. APPLICATIONS

- DC to DC converter.
- High voltage coupling/DC blocking.
- Back-lighting inverters.
- Snubbers in high frequency power converters.
- Power supplies.
- Surge protection.
- Filtering, smoothing, and decoupling application.

4. HOW TO ORDER

<u>FE</u>	<u>2H</u>	<u>X</u>	<u>105</u>	<u>K</u>	<u>631</u>	<u>E</u>	<u>D</u>	<u>L</u>
PDC Family	Chip q'ty and size	Dielectric	Capacitance	Tolerance	Rated Voltage	Packaging	Thickness	Control Code
Table1	Table2	Table3	Table4	Table5	Table6	Table7	Table8	Table9

Table 1	PDC family
Code	Description
FE	Stacked Capacitors Series

Table 2	Stack chip quantity and chip size				
The first digit : # of chips in stack					
Second digit code : chip size (below)					
Code	Description	Code	Description	Code	Description
A	1210 (3225)	G	1825 (4563)	I	2225 (5763)
C	1812 (4532)	H	2220 (5750)		

Table 3	Dielectric Material Characteristics		
Code	Description	Code	Description
N	COG	X	X7R

Table 4	Table 4 Capacitance Rule Code		
Code	Description	Code	Description
R47	0.47pF	102	$102=10 \times 10^2=1000\text{pF}$
OR5	0.5pF	104	$104=10 \times 10^4=100\text{nF}$
100	$100=10 \times 10^0=10\text{pF}$	106	$106=10 \times 10^6=10\mu\text{F}$

Table 5	Tolerance				
Code	Description	Code	Description	Code	Description
A	$\pm 0.05 \text{ pF}$	I	-10% ~ 0%	Q	$\pm 0.03 \text{ pF}$
B	$\pm 0.10 \text{ pF}$	J	$\pm 5 \%$	Z	-20% ~ +80%
C	$\pm 0.25 \text{ pF}$	K	$\pm 10 \%$	X	+10% ~ +20%
D	$\pm 0.50 \text{ pF}$	L	0% ~ +10%		
F	$\pm 1 \%$	M	$\pm 20 \%$		
G	$\pm 2 \%$	N	-5% ~ +10%		
H	$\pm 3 \%$	P	$\pm 0.02 \text{ pF}$		

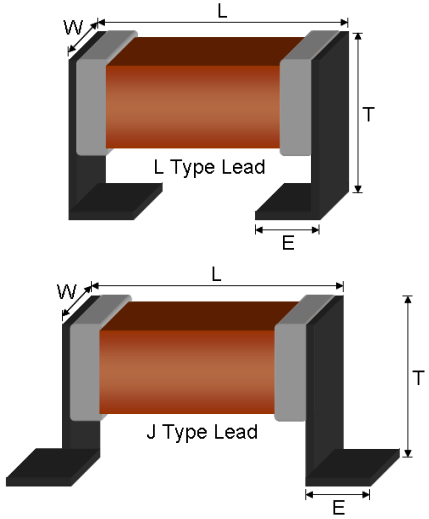
Table 6	Rated voltage				
Code	Description	Code	Description	Code	Description
500	50Vdc	251	250Vdc	102	1000Vdc
101	100Vdc	501	500Vdc		
201	200Vdc	631	630Vdc		

Table 7	Packaging Type		
Code	Description	Code	Description
B	Bulk	E	Tape and 7" Reel, Embossed Tape
T	Tray package	L	Tape and 13" Reel, Embossed Tape

Table 8	Thickness Description				
Code	Description	Code	Description	Code	Description
A	3.00±0.30 mm	J	7.80±0.30 mm	S	12.60±0.30 mm
B	3.60±0.30 mm	K	8.40±0.30 mm	T	13.20±0.30 mm
C	4.20±0.30 mm	L	9.00±0.30 mm		
D	4.80±0.30 mm	M	9.60±0.30 mm		
E	5.40±0.30 mm	N	10.20±0.30 mm		
F	6.00±0.30 mm	P	10.80±0.30 mm		
G	6.60±0.30 mm	Q	11.40±0.30 mm		
H	7.20±0.30 mm	R	12.00±0.30 mm		

Table 9	Special Control Code
Code	Description
L	L type lead
J	J type lead
S	Straight type lead

5. EXTERNAL DIMENSIONS

Size Inch (mm)	L (mm)	W (mm)	T (mm)	E (mm)	
1210 (3225)	3.50±0.40	2.50±0.40	Reference Table 8	1.70±0.15	 <p>Fig.5-1 The outline of Stacked Capacitors</p>
1812 (4532)	4.80±0.40	3.20±0.40		1.70±0.15	
1825 (4563)	4.80±0.40	6.30±0.50		1.70±0.15	
2220 (5750)	6.00±0.40	5.00±0.50		1.70±0.15	
2225 (5763)	6.00±0.40	6.30±0.50		1.70±0.15	

6. GENERAL ELECTRICAL DATA

Dielectric	C0G		X7R	
Size	1210, 1812, 1825, 2220, 2225		1210, 1812, 1825, 2220, 2225	
Rated voltage (WVDC)	50V, 100V, 200V, 250V, 500V, 630V, 1000V		50V, 100V, 200V, 250V, 500V, 630V, 1000V	
Capacitance range*	660nF Max.		44µF Max.	
Capacitance tolerance	Reference to Table5		Reference to Table5	
Tan δ	Cap. Range	Q Spec.	For 1 chip in stack≤2.5% For 2 chips in stack≤5.0%	
	Cap.<30pF:	Q≥400+20C		
	Cap≥30pF:	Q≥1000		
Capacitance & Tan δ Test condition	Measured at the condition of 30~70% related humidity		Measured at the condition of 30~70% related humidity	
	For 25°C at ambient temperature		Preconditioning for Class II MLCC : Perform a heat treatment at 150±10°C for 1 hour, then leave in ambient condition (25°C) for 24±2 hours before measurement	
	Cap. Range	Test Condition	Cap. Range	Test Condition
	Cap.≤1000pF	1.0±0.2Vrms, 1.0MHz±10%	Cap.≤10µF	1.0±0.2Vrms, 1.0KHz±10%
Cap.>1000pF	1.0±0.2Vrms, 1.0KHz±10%	Cap.>10µF	0.5±0.2Vrms, 120KHz±20%	
Insulation resistance at Ur	≥100GΩ or RxC≥500Ω-F, whichever is smaller		≥10GΩ or RxC≥100Ω-F, whichever is smaller	
Operating temperature	-55 to +125°C		-55 to +125°C	
Capacitance characteristic	±30ppm / °C		±15%	
Lead frame	L / J / Straight type lead		L / J / Straight type lead	

7. CAPACITANCE RANGE (Max.)

7-1. C0G

Dimension	Code	Rated Voltage						
		50V	100V	200V	250V	500V	630V	1000V
1210	1A	683	473	333	333	183	153	392
	2A	134	104	663	663	363	333(M)	782
1812	1C	154	104	563	563	393	333	562
	2C	334(M)	224(M)	124	124	783	663	123
1825	1G	154	124	104	104	683	683	123
	2G	334(M)	244	204	224(M)	134	134	243
2220	1H	274	184	104	104	683	563	123
	2H	544	364	224(M)	224(M)	134	124	243
2225	1I	334	224	154	154	104	823	123
	2I	664	444	334(M)	334(M)	224(M)	164	243

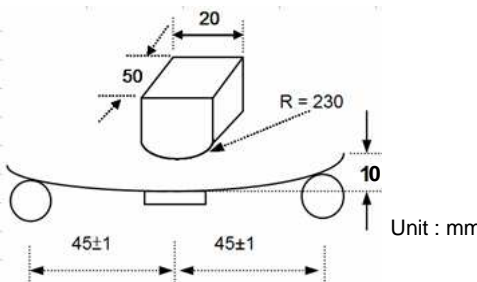
7-2. X7R

Dimension	Code	Rated Voltage						
		50V	100V	200V	250V	500V	630V	1000V
1210	1A	475	335	684	684	154	154	683
	2A	106	665	135	135	334(M)	334(M)	134
1812	1C	106	565	105	105	474	184	104
	2C	226(M)	126	225(M)	225(M)	105	364	224(M)
1825	1G	106	106	275	275	824	824	334
	2G	226(M)	226(M)	545	545	165	165	664
2220	1H	226	106	275	275	105	105	394
	2H	446	226(M)	545	545	225(M)	225(M)	784
2225	1I	226	106	395	395	155	155	394
	2I	446	226(M)	785	785	335(M)	335(M)	784

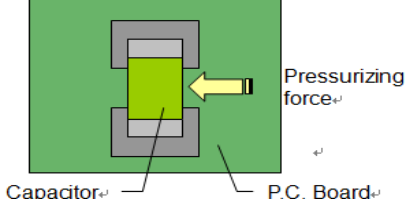
8. RELIABILITY TEST CONDITIONS AND REQUIREMENTS

No.	Item	Test Condition	Requirements																										
1.	Visual and Dimensions	---	* No remarkable defect. * Dimensions to confirm to individual specification sheet.																										
2.	Capacitance	---	* Shall not exceed the limits given in the detailed spec.																										
3.	Q/D.F. (Dissipation Factor)	* Class I : Cap. ≤ 1000pF, 1.0±0.2Vrms, 1MHz±10%. Cap. > 1000pF, 1.0±0.2Vrms, 1KHz±10%. * Class II : Cap. ≤ 10μF, 1.0±0.2Vrms, 1KHz±10%. Cap. > 10μF, 0.5±0.2Vrms, 120Hz±20%.	<table border="1"> <thead> <tr> <th>Dielectric</th> <th>Rated vol.(V)</th> <th>Q/D.F.</th> <th>Remark</th> </tr> </thead> <tbody> <tr> <td rowspan="2">Class I (C0G)</td> <td rowspan="2">All</td> <td>Q ≥ 1000</td> <td>Cap. ≥ 30pF</td> </tr> <tr> <td>Q ≥ 400+20C</td> <td>Cap. < 30pF</td> </tr> <tr> <td rowspan="2">Class II (X7R)</td> <td>1 chip in stack</td> <td>D.F. ≤ 2.5%</td> <td>---</td> </tr> <tr> <td>2 chips in stack</td> <td>D.F. ≤ 5.0%</td> <td>---</td> </tr> </tbody> </table>	Dielectric	Rated vol.(V)	Q/D.F.	Remark	Class I (C0G)	All	Q ≥ 1000	Cap. ≥ 30pF	Q ≥ 400+20C	Cap. < 30pF	Class II (X7R)	1 chip in stack	D.F. ≤ 2.5%	---	2 chips in stack	D.F. ≤ 5.0%	---									
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4.	Temperature Coefficient	* With no electrical load. <table border="1"> <thead> <tr> <th>T.C.</th> <th>Operating Temp</th> </tr> </thead> <tbody> <tr> <td>C0G</td> <td>-55~125°C at 25°C</td> </tr> <tr> <td>X7R</td> <td>-55~125°C at 25°C</td> </tr> </tbody> </table>	T.C.	Operating Temp	C0G	-55~125°C at 25°C	X7R	-55~125°C at 25°C	<table border="1"> <thead> <tr> <th>T.C.</th> <th>Capacitance Change</th> </tr> </thead> <tbody> <tr> <td>C0G</td> <td>Within ±30ppm/°C</td> </tr> <tr> <td>X7R</td> <td>Within ±15%</td> </tr> </tbody> </table>	T.C.	Capacitance Change	C0G	Within ±30ppm/°C	X7R	Within ±15%														
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7.	Temperature Cycle	* Conduct the 100 cycles according to the temperatures and time. <table border="1"> <thead> <tr> <th>Step</th> <th>Temp.(°C)</th> <th>Time(min.)</th> </tr> </thead> <tbody> <tr> <td>1</td> <td>Min. operating temp. +0/-3</td> <td>30±3</td> </tr> <tr> <td>2</td> <td>Room temp.</td> <td>2~3</td> </tr> <tr> <td>3</td> <td>Max. operating temp. +3/-0</td> <td>30±3</td> </tr> <tr> <td>4</td> <td>Room temp.</td> <td>2~3</td> </tr> </tbody> </table> * Before initial measurement (Class II only) : Perform 150+0/-10°C for 1 hr and then set for 48±4 hrs at room temp. * Measurement to be made after keeping at room temp. for 24±2 hrs (Class I) or 48±4 hrs (Class II).	Step	Temp.(°C)	Time(min.)	1	Min. operating temp. +0/-3	30±3	2	Room temp.	2~3	3	Max. operating temp. +3/-0	30±3	4	Room temp.	2~3	* No remarkable damage. <table border="1"> <thead> <tr> <th>Dielectric</th> <th>I.R.</th> <th>Cap. Change</th> <th>Q/D.F.</th> </tr> </thead> <tbody> <tr> <td>Class I (C0G)</td> <td rowspan="2">To meet initial requirement</td> <td>Within ±2.5% or ±0.25pF, whichever is larger</td> <td>≤ 1.0(Q) × initial requirement</td> </tr> <tr> <td>Class II (X7R)</td> <td>Within ±7.5%</td> <td>≤ 1.5(D.F.) × initial requirement</td> </tr> </tbody> </table>	Dielectric	I.R.	Cap. Change	Q/D.F.	Class I (C0G)	To meet initial requirement	Within ±2.5% or ±0.25pF, whichever is larger	≤ 1.0(Q) × initial requirement	Class II (X7R)	Within ±7.5%	≤ 1.5(D.F.) × initial requirement
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8.	Humidity (Damp Heat) Steady State	* Test temp. : 40±2°C. * Humidity : 90~95%RH. * Test time : 500 +24/-0 hrs. * Measurement to be made after keeping at room temp. for 24±2 hrs (Class I) or 48±4 hrs (Class II).	* No remarkable damage. <table border="1"> <thead> <tr> <th>Dielectric</th> <th>I.R.</th> <th>Cap. Change</th> <th colspan="2">Q/D.F.</th> </tr> </thead> <tbody> <tr> <td rowspan="2">Class I (C0G)</td> <td rowspan="2">≥ 1G or RxC ≥ 50Ω-F, whichever is smaller</td> <td rowspan="2">Within ±5.0% or ± 0.5pF, whichever is larger</td> <td>Cap. ≥ 30pF</td> <td>Q ≥ 350</td> </tr> <tr> <td>10pF ≤ Cap. < 30pF</td> <td>Q ≥ 275+2.5C</td> </tr> <tr> <td>Class II (X7R)</td> <td></td> <td>Within ±12.5%</td> <td colspan="2">D.F. ≤ 200% of initial requirement</td> </tr> </tbody> </table>	Dielectric	I.R.	Cap. Change	Q/D.F.		Class I (C0G)	≥ 1G or RxC ≥ 50Ω-F, whichever is smaller	Within ±5.0% or ± 0.5pF, whichever is larger	Cap. ≥ 30pF	Q ≥ 350	10pF ≤ Cap. < 30pF	Q ≥ 275+2.5C	Class II (X7R)		Within ±12.5%	D.F. ≤ 200% of initial requirement										
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9.	Humidity (Damp Heat) Load	<p>* Test temp. : 40±2°C. * Humidity : 90~95% RH. * Test time : 500 +24/-0hrs. * To apply voltage : Rated voltage (Max. 500Vdc). * Measurement to be made after keeping at room temp. for 24±2 hrs (Class I) or 48±4 hrs (Class II).</p>	<p>* No remarkable damage.</p> <table border="1"> <thead> <tr> <th>Dielectric</th> <th>I.R.</th> <th>Cap. Change</th> <th colspan="2">Q/D.F.</th> </tr> </thead> <tbody> <tr> <td rowspan="2">Class I (C0G)</td> <td rowspan="2">≥1GΩ or RxC≥50Ω-F, whichever is smaller</td> <td>Within ±7.5% or ±0.75pF, whichever is larger</td> <td>Cap.≥30pF</td> <td>Q≥350</td> </tr> <tr> <td></td> <td>10pF≤Cap.<30pF</td> <td>Q≥275+2.5C</td> </tr> <tr> <td>Class II (X7R)</td> <td></td> <td>Within ±12.5%</td> <td>Cap.<10pF</td> <td>Q≥200+10C</td> </tr> <tr> <td colspan="3"></td> <td colspan="2">D.F.≤200% of initial requirement</td> </tr> </tbody> </table>	Dielectric	I.R.	Cap. Change	Q/D.F.		Class I (C0G)	≥1GΩ or RxC≥50Ω-F, whichever is smaller	Within ±7.5% or ±0.75pF, whichever is larger	Cap.≥30pF	Q≥350		10pF≤Cap.<30pF	Q≥275+2.5C	Class II (X7R)		Within ±12.5%	Cap.<10pF	Q≥200+10C				D.F.≤200% of initial requirement																											
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10.	High Temperature Load (Endurance)	<p>* Test temp. : 125±3°C.</p> <table border="1"> <thead> <tr> <th>Dielectric</th> <th>Rated Vol.(V)</th> <th>Apply Voltage</th> </tr> </thead> <tbody> <tr> <td rowspan="4">C0G/X7R</td> <td>≤250</td> <td>2.0 times of U_R</td> </tr> <tr> <td>250<V≤ 500</td> <td>1.5 times of U_R</td> </tr> <tr> <td>=630</td> <td>1.2 times of U_R</td> </tr> <tr> <td>=1000</td> <td>1.1 times of U_R</td> </tr> </tbody> </table> <p>* Exception items (X7R only) :</p> <table border="1"> <thead> <tr> <th>Rated Vol.(V)</th> <th>Size</th> <th>Cap. Range (Single chip)</th> <th>Apply Voltage</th> </tr> </thead> <tbody> <tr> <td rowspan="6">50 & 100</td> <td>0805</td> <td>≥124</td> <td rowspan="6">1.5 times of U_R</td> </tr> <tr> <td>1206</td> <td rowspan="5">≥105</td> </tr> <tr> <td>1210</td> </tr> <tr> <td>1812</td> </tr> <tr> <td>1825</td> </tr> <tr> <td>2220</td> </tr> <tr> <td>2225</td> <td></td> </tr> <tr> <td rowspan="5">200 & 250</td> <td>1210</td> <td>>224</td> <td rowspan="5">1.5 times of U_R</td> </tr> <tr> <td>1812</td> <td>>474</td> </tr> <tr> <td>1825</td> <td rowspan="3">≥105</td> </tr> <tr> <td>2220</td> </tr> <tr> <td>2225</td> </tr> </tbody> </table> <p>* Test time : 1000 +24/-0 hrs. * Measurement to be made after keeping at room temp. for 24±2 hrs (Class I) or 48±4 hrs (Class II).</p>	Dielectric	Rated Vol.(V)	Apply Voltage	C0G/X7R	≤250	2.0 times of U _R	250<V≤ 500	1.5 times of U _R	=630	1.2 times of U _R	=1000	1.1 times of U _R	Rated Vol.(V)	Size	Cap. Range (Single chip)	Apply Voltage	50 & 100	0805	≥124	1.5 times of U _R	1206	≥105	1210	1812	1825	2220	2225		200 & 250	1210	>224	1.5 times of U _R	1812	>474	1825	≥105	2220	2225	<p>* No remarkable damage.</p> <table border="1"> <thead> <tr> <th>Dielectric</th> <th>I.R.</th> <th>Cap. Change</th> <th>Q/D.F.</th> </tr> </thead> <tbody> <tr> <td>Class I (C0G)</td> <td>≥1GΩ or RxC≥50Ω-F, whichever is smaller</td> <td>Within ± 3.0% or ± 0.3pF, whichever is larger</td> <td rowspan="2">D.F.≤200% of initial requirement</td> </tr> <tr> <td>Class II (X7R)</td> <td></td> <td>Within ±12.5%</td> </tr> </tbody> </table>	Dielectric	I.R.	Cap. Change	Q/D.F.	Class I (C0G)	≥1GΩ or RxC≥50Ω-F, whichever is smaller	Within ± 3.0% or ± 0.3pF, whichever is larger	D.F.≤200% of initial requirement	Class II (X7R)		Within ±12.5%
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11.	Resistance to Flexure of Substrate	<p>* The middle part of substrate shall be pressurized by means of the pressurizing rod at a rate of about 1mm per second until the deflection becomes 10mm.</p> 	<p>* No remarkable damage.</p> <table border="1"> <thead> <tr> <th>Dielectric</th> <th>Cap. Change</th> </tr> </thead> <tbody> <tr> <td>Class I (C0G)</td> <td>Within ±3.0% or ±0.3pF, whichever is larger</td> </tr> <tr> <td>Class II (X7R)</td> <td>Within ±12.5%</td> </tr> </tbody> </table> <p>(This capacitance change means the change of capacitance under specified flexure of substrate from the capacitance measured before the test)</p>	Dielectric	Cap. Change	Class I (C0G)	Within ±3.0% or ±0.3pF, whichever is larger	Class II (X7R)	Within ±12.5%																																											
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8. RELIABILITY TEST CONDITIONS AND REQUIREMENTS

No.	Item	Test Condition	Requirements
12.	Adhesive Strength of Termination	<p>* Capacitors mounted on a substrate. A force of 10N applied perpendicular to the place of substrate and parallel the line joining the center of terminations for 10±1 second.</p> 	* No remarkable damage or removal of the terminations.
13.	Vibration Resistance	<p>* Vibration frequency : 10~55 Hz/min. * Total amplitude : 1.5mm. * Test time : 6 hrs. (Two hours each in three mutually perpendicular directions)</p>	<p>* No remarkable damage. * Cap. change and Q/D.F. : To meet initial spec.</p>

9. APPLICATION NOTES

STORAGE

To prevent the damage of solderability of terminations, the following storage conditions are recommended :

Indoors under 5 ~ 40°C and 20% ~ 70% RH.

No harmful gases containing sulfuric acid, ammonia, hydrogen sulfide or chlorine.

Packaging should not be opened until the capacitors are required for use. If opened, the pack should be re-sealed as soon as is practicable. Taped product should be stored out of direct sunlight, which might promote deterioration in tape or adhesion performance. The product is recommended to be used within 12 months after shipment and checked the solderability before use.

HANDLING

Chip capacitors are dense, hard, brittle, and abrasive materials. They are liable to suffer mechanical damage, in the form of cracks or chips. Chip Capacitors should be handled with care to avoid contamination or damage. To use vacuum or plastic tweezers to pick up or plastic tweezers is recommended for manual placement. Tape and reeled packages are suitable for automatic pick and placement machine.

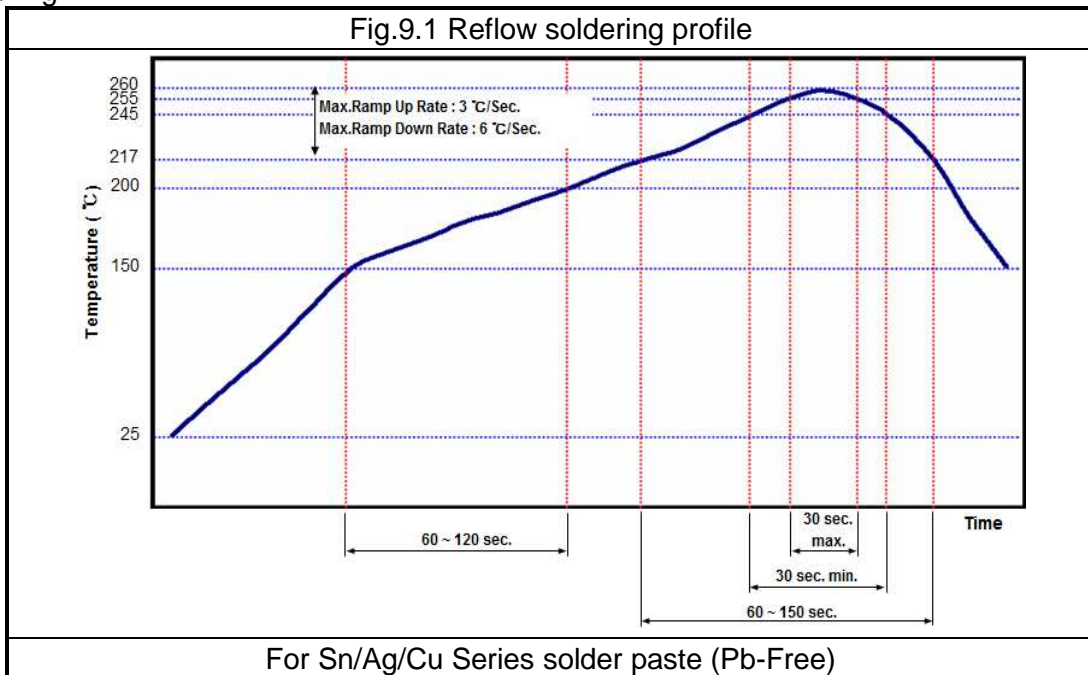
PREHEAT

In order to minimize the risk of thermal shock during soldering, a carefully controlled preheat is required. The rate of preheat should not exceed 3°C per second.

SOLDERING

Use mildly activated rosin RA and RMA fluxes do not use activated flux. The amount of solder in each solder joint should be controlled to prevent the damage of chip capacitors caused by the stress between solder, chips, and substrate.

a.) Reflow soldering :



COOLING

After soldering, cool the chips and the substrate gradually to room temperature. Natural cooling in air is recommended to minimize stress in the solder joint.

9. APPLICATION NOTES

CLEANING

All flux residues must be removed by using suitable electronic-grade vapor-cleaning solvents to eliminate contamination that could cause electrolytic surface corrosion. Good results can be obtained by using ultrasonic cleaning of the solvent. The choice of the proper system is depends upon many factors such as component mix, flux, and solder paste and assembly method. The ability of the cleaning system to remove flux residues and contamination from under the chips is very important.